

Cascaded superconducting junction refrigerators: Optimization and performance limits

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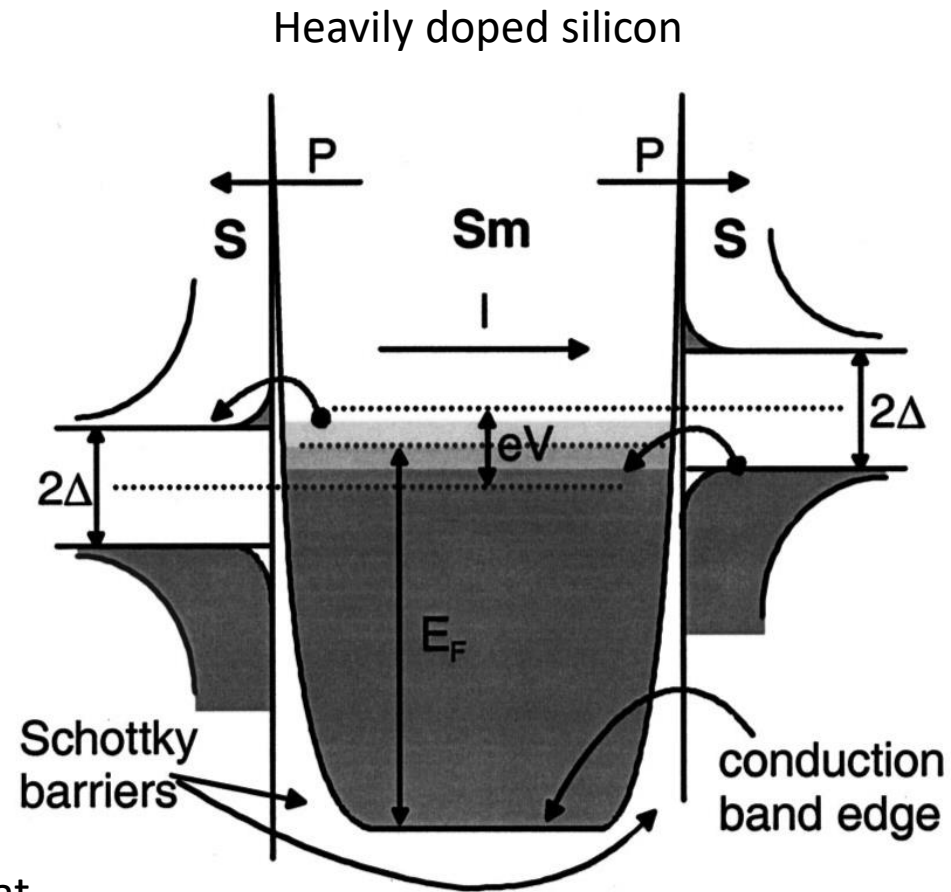
AFFILIATIONS

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Metallurgical Schottky contact at S-Sm forms a tunnel barrier

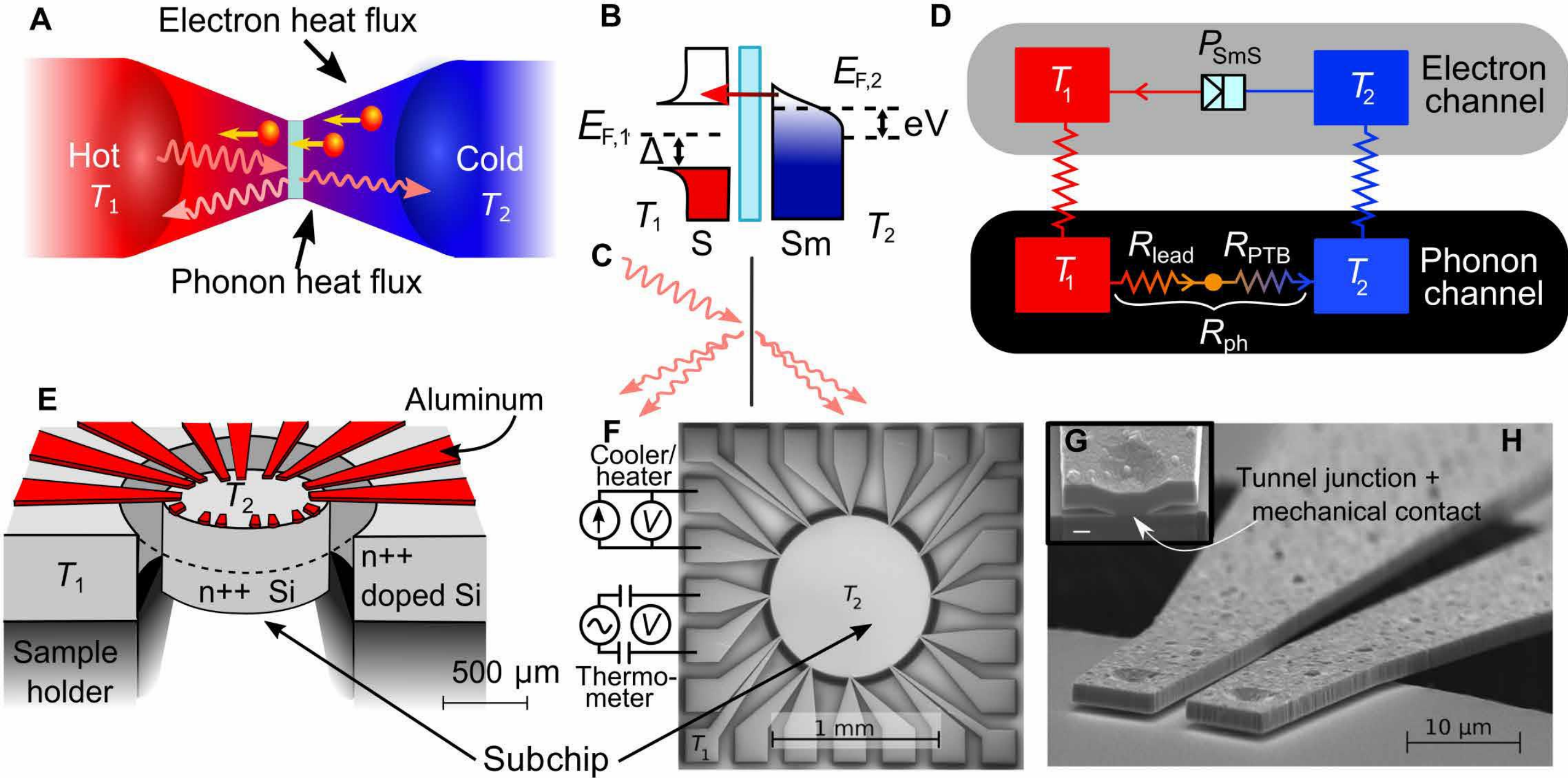
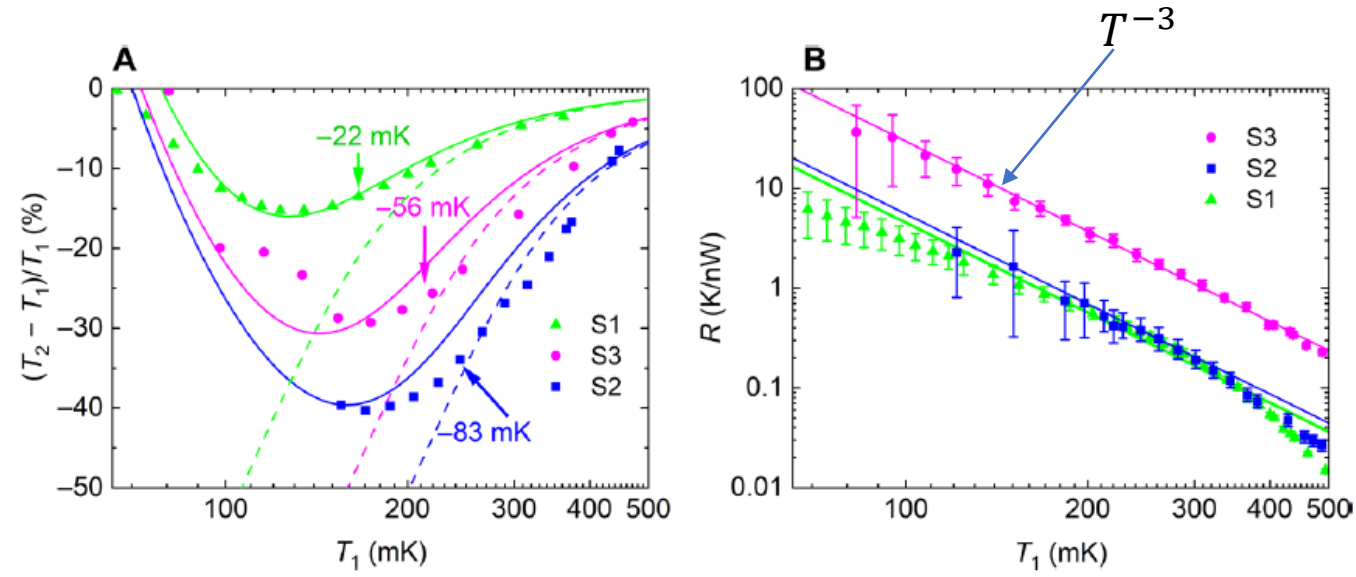


Table 1. Sample parameters and literature values for thermal boundary resistance. Here, A is the area of a tunnel junction, d is the diameter of the subchip, $R_A = R_T A$ is the characteristic junction resistance, and R_T is the junction resistance. Thermal resistance prefactors (α) are the values obtained from the fits of Fig. 2, whereas α_{AMM} and α_{DMM} correspond to theoretical R_{PTB} (35).

Sample	A μm^2	d μm	$R_A = R_T A$ $\Omega\mu\text{m}^2$	α $\text{K}^4/\mu\text{W}$	α_{AMM} $\text{K}^4/\mu\text{W}$	α_{DMM} $\text{K}^4/\mu\text{W}$	Max cooling %	Max cooling mK
S1	2.0/137*	300	538	4.5	–	–	15 (@ 140 mK)	22 (@ 166 mK)
S2	7.5	1000	476	5.6	6.5	8.8	40 (@ 170 mK)	83 (@ 244 mK)
S3	3.2	300	1945	29	16	21	29 (@ 173 mK)	56 (@ 220 mK)

*Sample S1 had silicon oxide between leads and subchip, and therefore, the effective area of the phononic heat contact, $137 \mu\text{m}^2$, is larger than the junction area $2.0 \mu\text{m}^2$.



Conclusions

1. Since cooling power and phonon leaks are proportional to A , one should decrease $R_A = R_T A$
2. Suppression of phonon thermal conductivity above 500 mK requires “phonon engineering”
3. Above 500 mK, a superconductor with larger Δ is required. Vanadium.

$$P_{\Sigma 2} = P_{H3} - P_{C2} + P_{L2} - P_{L3}$$

Progressively smaller area is good

$$P_{H3} = P_{C3} \propto A_3$$

Less efficient at high T

$$P_L \propto T^4$$

$$P_C \propto T^2$$

R_0 is sub-gap leakage resistance

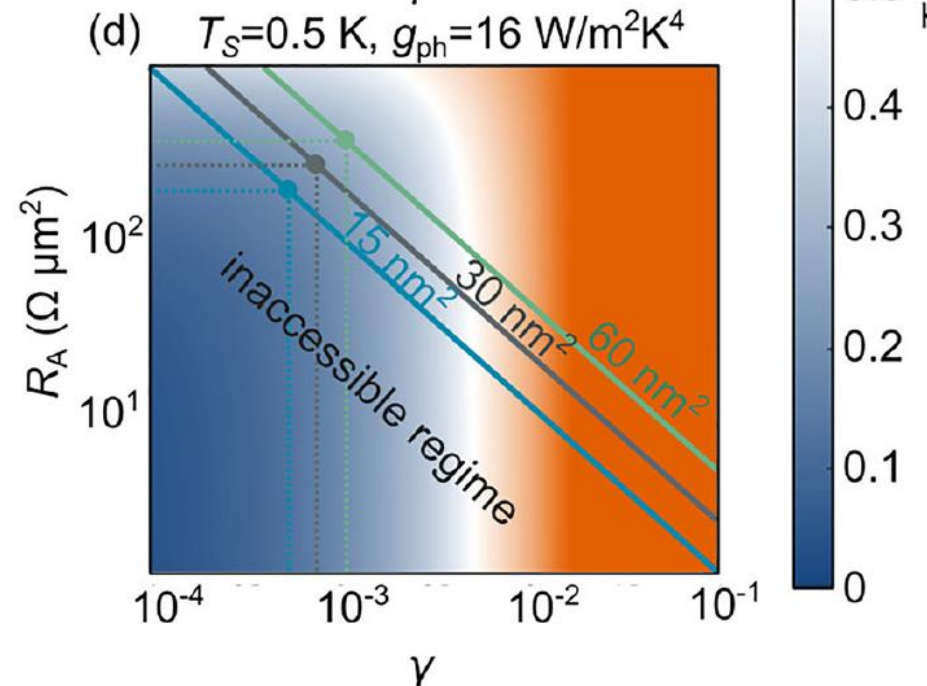
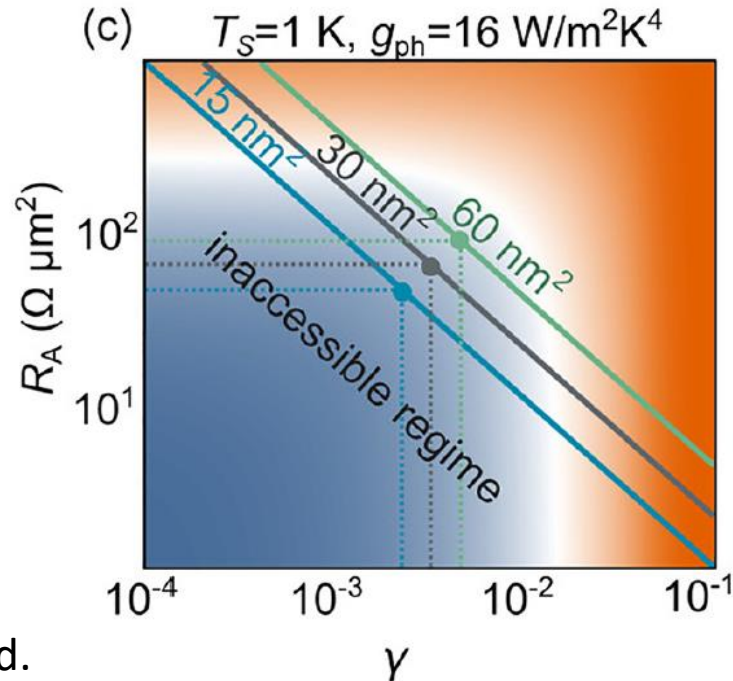
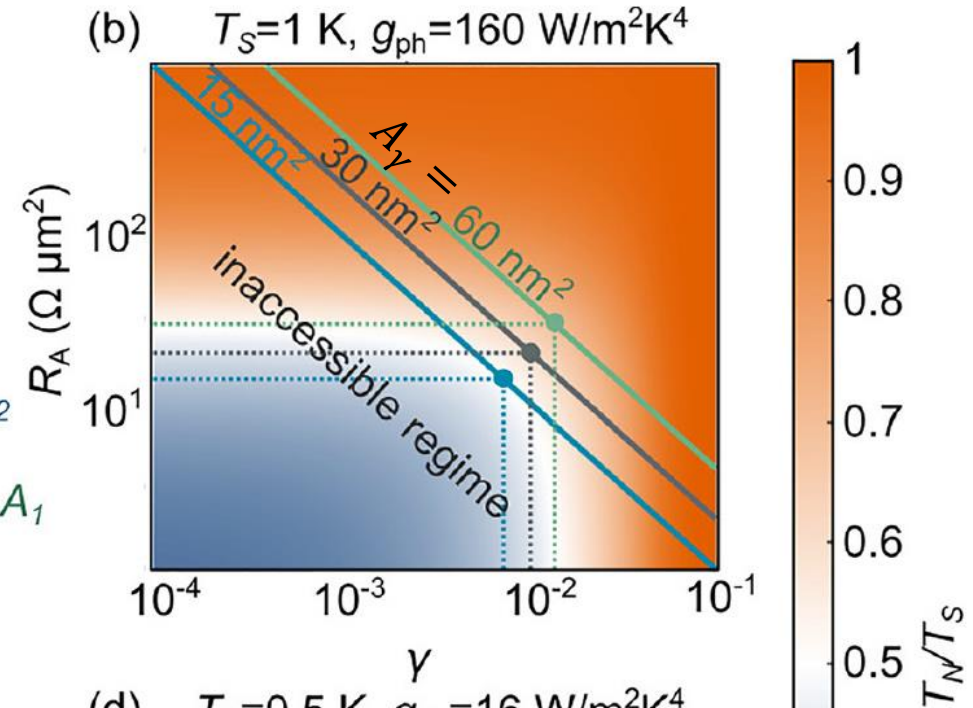
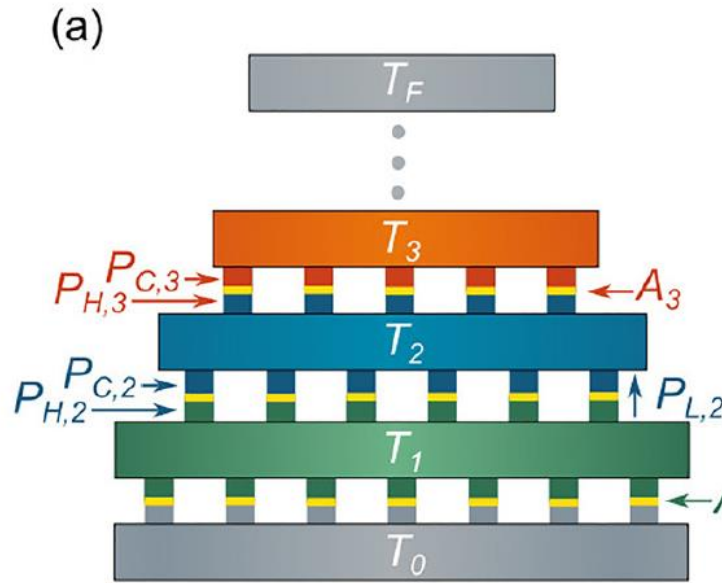
A_{ch} is effective tunneling area/ G_0

$$\gamma = \frac{R_0}{R_T} = \frac{A_{ch} R_K}{4R_A}$$

$$P_L = g_{ph} A (T_S - T_N)^4$$

$$A_\gamma = \frac{4\gamma R_A}{R_K} \text{ phenomen. leakage area}$$

Lower R_A at the cost of high γ is preferred.



A good refrigerator is energy efficient too.

Sufficient cooling power:

$$\frac{T_N^2}{T_S^2} \cong \frac{P_C}{P_H}$$

Maximum heat load: $P_{in} = P_C - P_L$

$$a = \frac{A_{n-1}}{A_n} = \frac{P_H T_N^2}{P_{in} T_S^2}$$

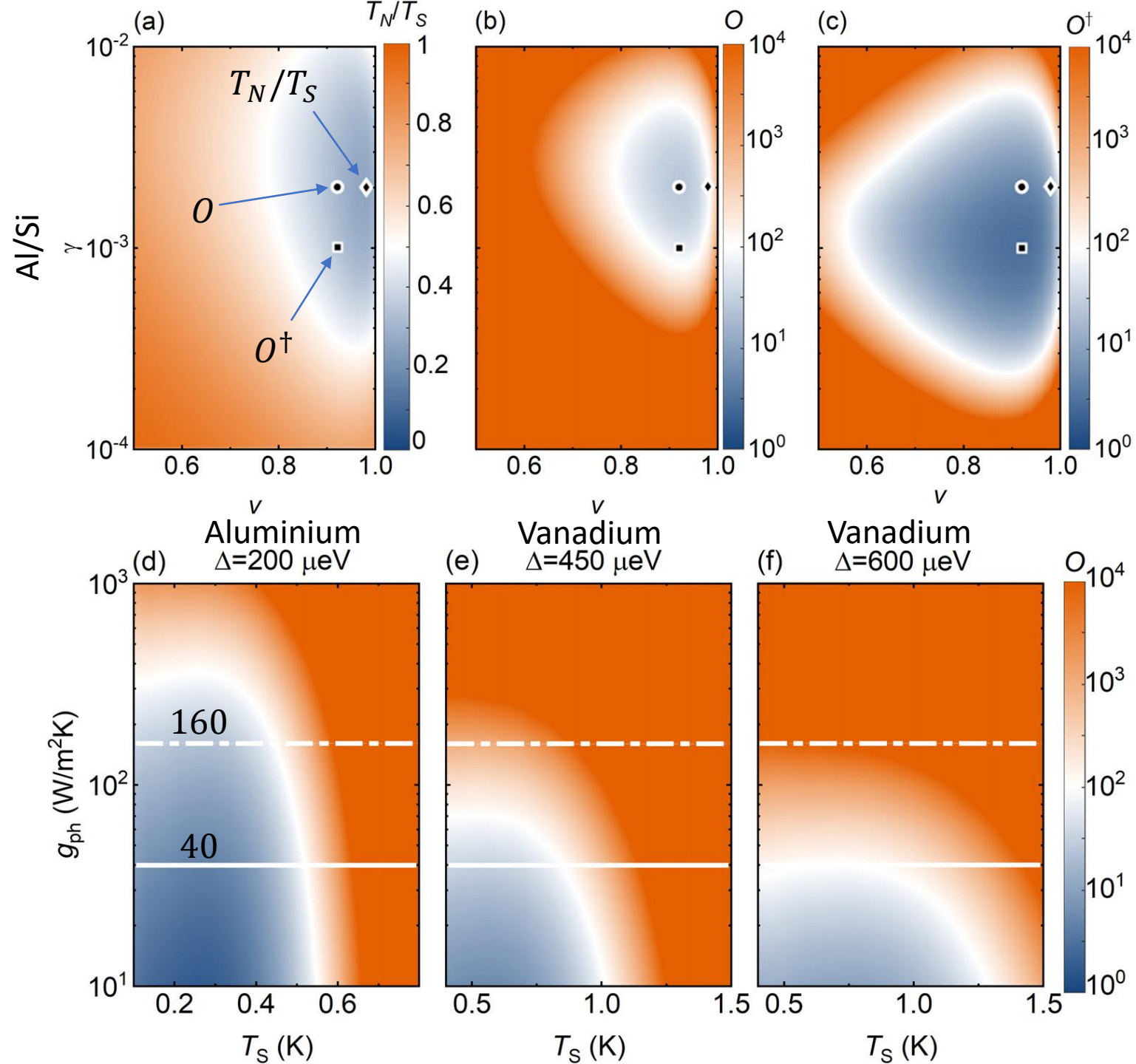
$$O = a^{1/\log(T_S/T_N)}$$

For small phonon leak (low T or good ph-filtering):

$$a^\dagger = \frac{P_H T_N^2}{P_C T_S^2}$$

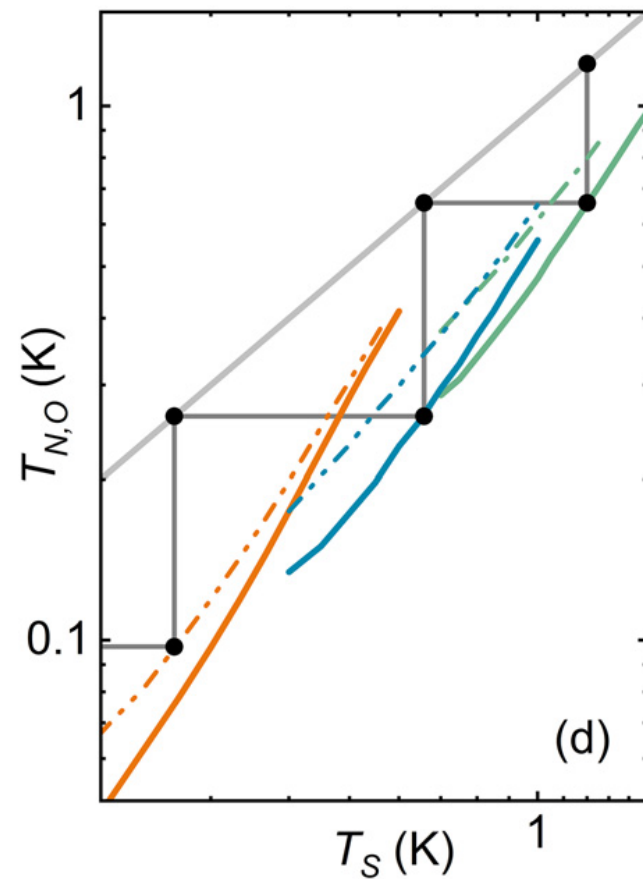
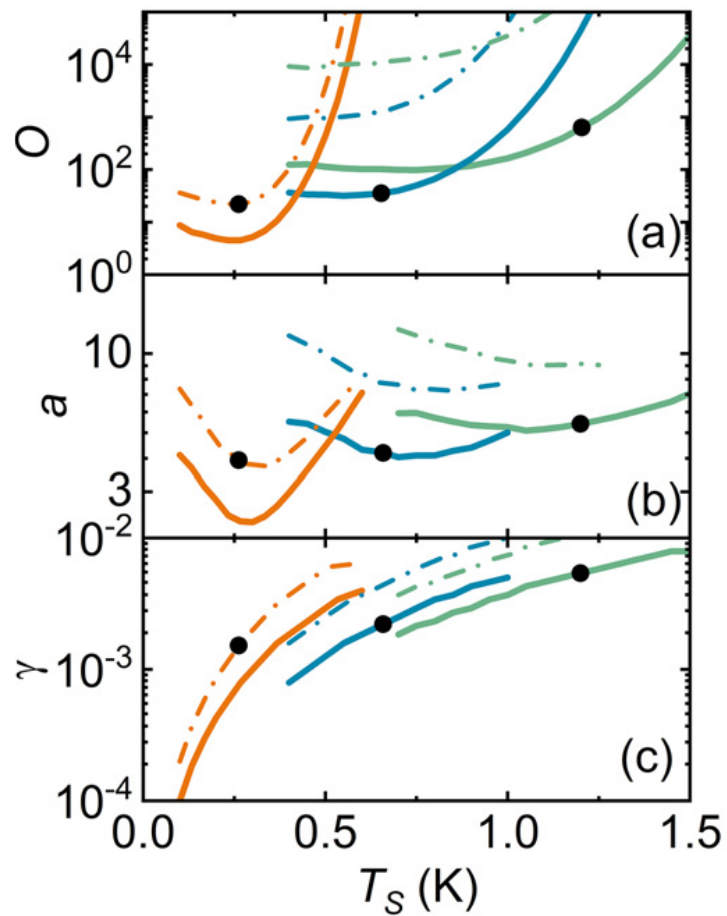
$$O^\dagger = a^\dagger^{1/\log(T_S/T_N)}$$

Minimization parameters: $v, \gamma, g_{ph}, T_S, T_N$



The Plan

$\Delta = 200 \mu\text{eV}$
 $\Delta = 450 \mu\text{eV}$
 $\Delta = 600 \mu\text{eV}$



n	g_{ph} (W/m ² K ⁴)	A_n/A_3		γ (10 ⁻³)		ν		T (m K)	
		A	B	A	B	A	B	A	B
1	40	32	90	5	5	0.88	0.94	598	571
2	40	8	17	2	1.6	0.94	0.98	196	161
3	160	1	1	0.8	0.6	0.96	0.98	89	91